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(54) CIRCUIT PROTECTED FROM OVERCURRENT

(57) Abstract:

tween the collector and the emitter. By this method, a transistor 2 is branched and becomes small and finally stops flowing. Therefore, the transistor 2 is cut off be-HAYASHI SHIGEO

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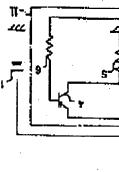
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rent and a reverse voltage.

power circuit can be protected from both an overcur-



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transistor with a second transistor connected to the nected to a transistor 2. When a short occurs in a load circuit due to the breakage or other troubles of a cable tor and an emitter of the transistor 2. Thereupon, the PURPOSE: To pratect 4 power circuit from both an overcurrent and a reverse voltage by controlling a first CONSTITUTION: A PNP-type transistor 4 is conand then a current running in the load circuit increases, a potential difference is generated between a connecpatential of a cathode of a diode 3 drops and a potenfirst transistor.

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